

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|------------------------------------|------------------|
| 1 | 11 | "semiconductor memory device" and ("first region" near2 "first direction") | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:57 |
| 2 | 10 | ("semiconductor memory device" and ("first region" near2 "first direction")) and "second region" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:42 |
| 5 | 20 | "word line" and ("first region" near2 "first direction") | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:46 |
| 7 | 19 | ("word line" and ("first region" near2 "first direction")) and select\$8 | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:47 |
| 8 | 12 | (("word line" and ("first region" near2 "first direction")) and select\$8) and activat\$8 | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:47 |
| 9 | 9 | ((("word line" and ("first region" near2 "first direction")) and select\$8) and activat\$8) and "sense amplifier" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:57 |
| 10 | 346 | "semiconductor memory device" and "open bit line" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:58 |
| 11 | 16 | ("semiconductor memory device" and "open bit line") and "first region" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:58 |
| 12 | 61 | ("semiconductor memory device" and "open bit line") and "first direction" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:58 |
| 13 | 55 | ("semiconductor memory device" and "open bit line") and "second direction" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:58 |
| 14 | 16 | ("semiconductor memory device" and "open bit line") and "second region" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:58 |
| 15 | 8 | (("semiconductor memory device" and "open bit line") and "second region") and perpendicular | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:59 |
| 16 | 2 | ((("semiconductor memory device" and "open bit line") and "first region") and ((semiconductor memory device" and "open bit line") and "first direction") and ((semiconductor memory device" and "open bit line") and "second direction") and ((semiconductor memory device" and "open bit line") and "second region") and (((semiconductor memory device" and "open bit line") and "second region") and perpendicular) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:59 |
| - | 1 | "20040017716" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:05 |
| - | 4 | (("6639822") or ("6545897") or ("6373776") or ("6370054")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 01:56 |
| - | 5 | ((("6639822") or ("6545897") or ("6373776") or ("6370054")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:02 |

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|-------|-------|---|------------------------------------|------------------|
| | 2 | "20030112695" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 01:58 |
| | 2 | "20010009519" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:00 |
| | 2 | "20020080640" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:01 |
| | 5 | "20040017716" or "20030112695" or "20010009519" or "20020080640" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:01 |
| | 9 | ("20040017716" or "20030112695" or "20010009519" or "20020080640") or (((("6639822") or ("6545897") or ("6373776") or ("6370054")).PN.) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:02 |
| 37122 | 37122 | "semiconductor memory device" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:06 |
| | 17 | "semiconductor memory device" and ("first region" near4 "first direction") | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/22 16:41 |
| | 47 | "semiconductor memory device" and first adj2 region adj6 first adj2 direction | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:09 |
| | 41 | ("semiconductor memory device" and first adj2 region adj6 first adj2 direction) and second adj2 direction | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:10 |
| | 210 | "semiconductor memory device" and "second direction perpendicular" near3 "first direction" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:11 |
| | 209 | "semiconductor memory device" and "second direction perpendicular" adj3 "first direction" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:13 |
| | 1 | "semiconductor memory device" and "selected first region" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:14 |
| | 42 | "semiconductor memory device" and select\$6 adj2 first adj2 region | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:14 |
| | 19 | ("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:15 |
| | 19 | ("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/02/20 02:15 |
| | 13 | ("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region | USPAT | 2004/02/20 02:15 |
| | 6 | ("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region | US-PGPUB | 2004/02/20 03:02 |